

**Amendments To The Claims:**

Claims 1-5, 7-11 and 18-28 are pending in the application. Claim 11 is a withdrawn method claim.

Please cancel claims 10 and 24-27 and amend claims 1, 11, 19, 22 and 28 as follows:

1. (Currently amended) A polishing composition used in precision polishing a wafer surface, the polishing composition comprising:

colloidal silica, wherein an average primary particle diameter  $D_{SA}$  of the colloidal silica, which is obtained from a specific surface area of the colloidal silica measured by a BET method, is from 5 to 30 nm; wherein an average secondary particle diameter  $D_{N4}$  of the colloidal silica, which is measured by a laser scattering method, is from 5 to 120 nm;

an alkaline compound, wherein the alkaline compound is ammonia;

a water-soluble polymer; and

water.

2. (Previously presented) The polishing composition according to claim 1, wherein the average primary particle diameter  $D_{SA}$  of the colloidal silica is from 5 to 25 nm.

3. (Previously presented) The polishing composition according to claim 2, wherein the average primary particle diameter  $D_{SA}$  of the colloidal silica is from 5 to 20 nm.

4. (Original) The polishing composition according to claim 1, wherein the average secondary particle diameter  $D_{N4}$  of the colloidal silica is from 5 to 100 nm.

5. (Original) The polishing composition according to claim 4, wherein the average secondary particle diameter  $D_{N4}$  of the colloidal silica is from 5 to 80 nm.

6. (Canceled)

7. (Original) The polishing composition according to claim 1, wherein the water-soluble polymer is at least one selected from hydroxyethyl cellulose, polyvinyl alcohol, and polyethylene

oxide.

8. (Original) The polishing composition according to claim 7, wherein the water-soluble polymer is hydroxyethyl cellulose.

9. (Original) The polishing composition according to claim 8, wherein content of the hydroxyethyl cellulose in the polishing composition is from 0.005 to 1.5 wt%.

10. (Canceled)

11 (Withdrawn - Currently amended) A method of polishing a wafer, the method comprising:

preparing a polishing composition, wherein the polishing composition includes:

colloidal silica,

wherein an average primary particle diameter  $D_{SA}$  of the colloidal silica, which is obtained from a specific surface area of the colloidal silica measured by a BET method, is from 5 to 30 nm; wherein an average secondary particle diameter  $D_{N4}$  of the colloidal silica, which is measured by a laser scattering method, is from 5 to 120 nm;

an alkaline compound, wherein the alkaline compound is ammonia;

a water-soluble polymer; and

water; and

precision polishing a surface of the wafer using the polishing composition.

12-17. (Canceled)

18. (Previously presented) The polishing composition according to claim 1, wherein the content of colloidal silica in the polishing composition is from 0.1 to 40 wt%.

19. (Currently amended) The polishing composition according to claim 1 18, wherein the content of colloidal silica in the polishing composition is from 0.1 to 1 wt% ~~1 to 20 wt%~~.

20. (Previously presented) The polishing composition according to claim 8, wherein the content of the hydroxyethyl cellulose in the polishing composition is from 0.05 to 0.5 wt%.

21. (Previously presented) The polishing composition according to claim 8, wherein the average molecular weight of the hydroxyethyl cellulose is from 300,000 to 3,000,000.

22. (Currently amended) The polishing composition according to claim 1 ~~claim 10~~, wherein, ~~when the alkaline compound is at least one of potassium hydroxide, sodium hydroxide, ammonia, and tetramethylammonium hydroxide,~~ the content of the alkaline compound in the polishing composition is from 0.01 to 8 wt%.

23. (Previously presented) The polishing composition according to claim 22, wherein the content of the alkaline compound in the polishing composition is from 0.1 to 3 wt%.

24-27. (Canceled)

28. (Currently amended) A polishing composition used in precision polishing a wafer surface, the polishing composition comprising:

colloidal silica, wherein an average primary particle diameter  $D_{SA}$  of the colloidal silica, which is obtained from a specific surface area of the colloidal silica measured by a BET method, is from 5 to 20 nm, wherein an average secondary particle diameter  $D_{N4}$  of the colloidal silica, which is measured by a laser scattering method, is from 5 to 80 nm, and wherein the content of colloidal silica in the polishing composition is from 0.1 to 40 wt%;

an alkaline compound, wherein the alkaline compound is ~~at least one selected from potassium hydroxide, sodium hydroxide, ammonia, tetramethylammonium hydroxide, anhydrous piperazine, and piperazine hexahydrate;~~

a water-soluble polymer, wherein the water-soluble polymer is at least one selected from hydroxyethyl cellulose, polyvinyl alcohol, and polyethylene oxide; and

water.